

NCE N-Channel Enhancement Mode Power MOSFET

Description

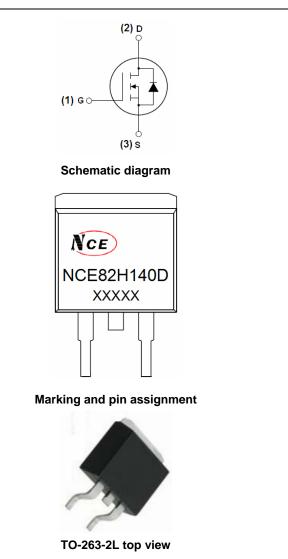
The NCE82H140D uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = 82V, I_D = 140A$ $R_{DS(ON)} < 5.2m\Omega @ V_{GS} = 10V$ (Typ:4.3m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



100% UIS TESTED!

100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE82H140D	NCE82H140D	TO-263-2L	-	-	-

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	82	V	
Gate-Source Voltage	Vgs	±20	V	
Drain Current-Continuous	Ι _D	140	А	
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	99	А	
Pulsed Drain Current (Note 1)	I _{DM}	480	А	
Maximum Power Dissipation	PD	220	W	
Derating factor		1.47	W/°C	
Single pulse avalanche energy (Note 5)	E _{AS}	1500	mJ	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	



Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{ extsf{ heta}Jc}$	0.68	°C/W
Thermal Resistance, Junction-to-Ambient (Note 2)	R_{\thetaJA}	60	°C /W

Electrical Characteristics (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	· ·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	82	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =82V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS} V _{GS} =±20V,V _{DS} =0V		-	-	±100	nA
On Characteristics (Note 3)	i i					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, I _D =250µA	2.5	3	3.8	V
Drain-Source On-State Resistance	R _{DS(ON)}	V_{GS} =10V, I _D =20A	-	4.3	5.2	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =20A		-	-	S
Dynamic Characteristics (Note4)			·			
Input Capacitance	C _{lss}		-	7900	-	PF
Output Capacitance	C _{oss}	V _{DS} =40V,V _{GS} =0V, F=1.0MHz	-	445	-	PF
Reverse Transfer Capacitance	C _{rss}		-	384	-	PF
Switching Characteristics (Note 4)	· ·					
Turn-on Delay Time	t _{d(on)}		-	23	-	nS
Turn-on Rise Time	tr	V_{DD} =30V, R _L =1 Ω	-	42	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =2.5 Ω	-	75	-	nS
Turn-Off Fall Time	t _f		-	26	-	nS
Total Gate Charge	Qg	V =40V(1 =20A	-	158	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =40V,I _D =20A, V _{GS} =10V	-	32	-	nC
Gate-Drain Charge	Q _{gd}	VGS-IUV	-	51	-	nC
Drain-Source Diode Characteristics	· · · ·		-			
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =140A	-	-	1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	140	Α
Reverse Recovery Time	trr	TJ = 25°C, IF = 20A	-	50	_	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	110	-	nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t \leq 10 sec.

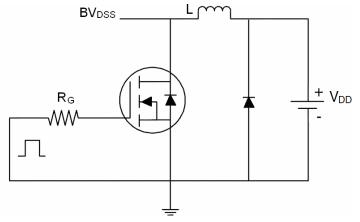
3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production
5. EAS condition: Tj=25°C,VDD=40V,VG=10V,L=0.5mH,Rg=25Ω

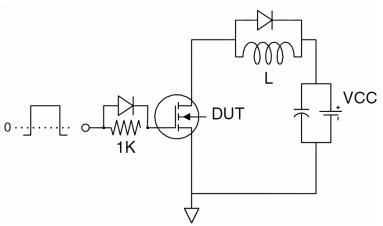


Test circuit

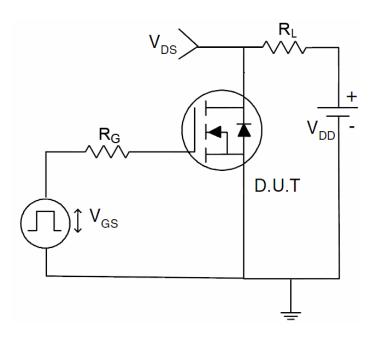
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





100 125

125

25° С

0.8

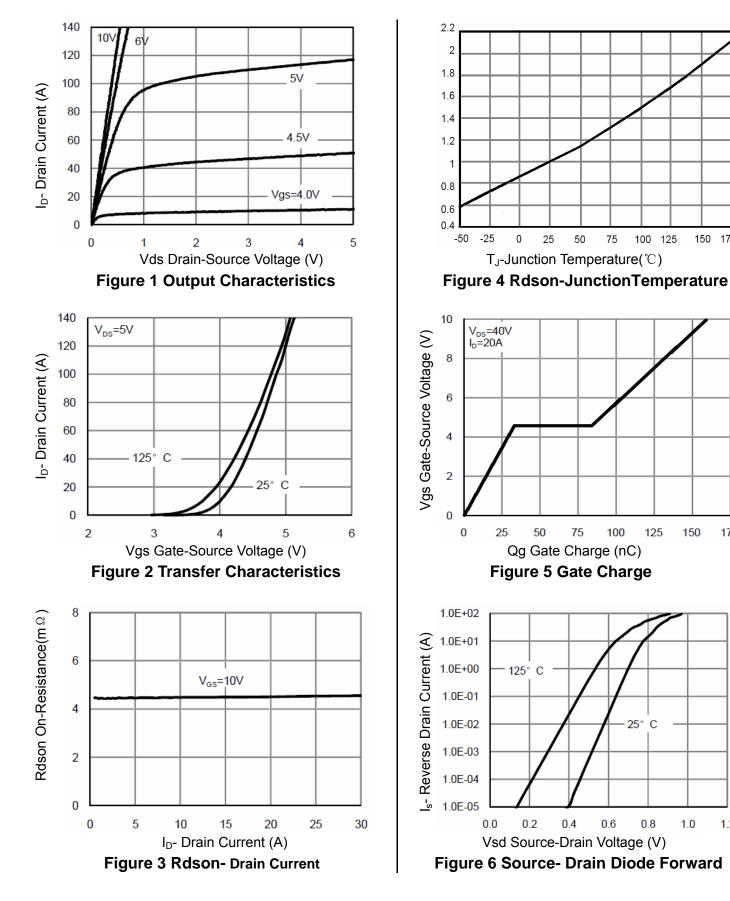
1.0

150

175

150 175

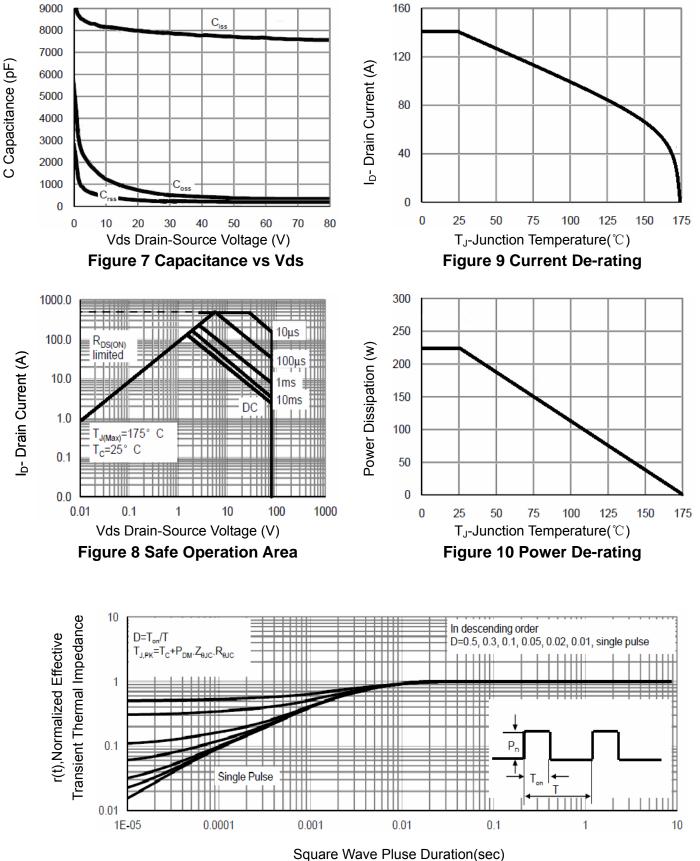
Typical Electrical and Thermal Characteristics (Curves)



1.2



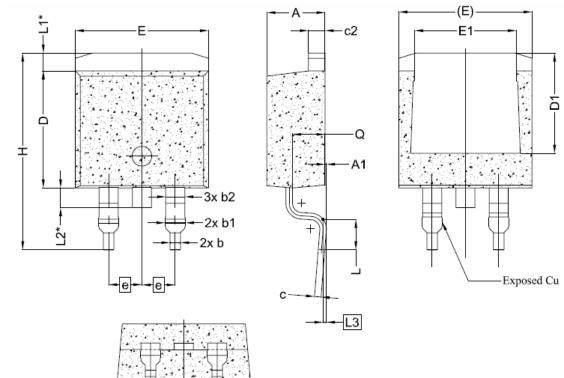
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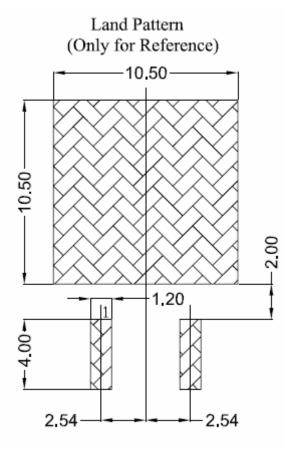


TO-263-2L Package Information



Symbol	Dimensions In Millimeters			
Symbol	Min.	Nom.	Max.	
A	4.24	4.44	4.64	
A1	0.00 0.10		0.25	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
с	0.40	0.50	0.60	
c2	1.15	1.27	1.40	
D	8.82	8.92	9.02	
D1	6.86	7.65	-	
E	9.96	10.16	10.36	
E1	6.89	7.77	7.89	
е	2.54BSC			
Н	14.61	15.00	15.88	
L	1.78 2.32		2.79	
L1	1.36 REF.			
L2	1.50 REF.			
L3	0.25 BSC			
Q	2.30	2.48	2.70	







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